

IN THE CLAIMS

Please amend the claims as follows:

- A7
- 8 (Amended) An alignment method comprising the steps of:
- a) preparing a reference-layer-defining photomask on which a first on-mask alignment accuracy measuring mark and an on-mask alignment mark have been formed, the first on-mask alignment accuracy measuring mark having a size equal to that of a first on-wafer intended pattern for a reference layer, the on-mask alignment mark having a size equal to that of a second on-wafer intended pattern to be defined in a layer-to-be-aligned;
 - b) preparing a layer-to-be-aligned-defining photomask that includes at least a second on-mask intended pattern for defining the second on-wafer intended pattern in the layer-to-be-aligned;
 - c) forming the first on-wafer intended pattern and an on-wafer alignment accuracy measuring mark on a wafer by using the reference-layer-defining photomask, the on-wafer alignment accuracy measuring mark being formed by transferring the on-mask alignment accuracy measuring mark; and
 - d) aligning the layer-to-be-aligned-defining photomask by reference to the position of the on-wafer alignment accuracy measuring mark for the reference layer.
- Sub B7